

Contents

1	Block diagram and pin description	5
2	Electrical specifications	7
2.1	Absolute maximum ratings	7
2.2	Thermal data	8
2.3	Electrical characteristics	8
2.4	Electrical characteristics curves	15
3	Application information	18
3.1	GND protection network against reverse battery	18
3.1.1	Solution 1: a resistor in the ground line (RGND only)	18
3.1.2	Solution 2: a diode (D _{GND}) in the ground line	19
3.2	Load dump protection	19
3.3	MCU I/O protection	19
3.4	Open load detection in off state	20
3.5	Maximum demagnetization energy (V _{CC} = 13.5V)	21
4	Package and PCB thermal data	22
4.1	SO-28 thermal data	22
5	Package and packing information	25
5.1	ECOPACK® packages	25
5.2	SO-28 packing information	26
6	Revision history	27

List of tables

Table 1.	Device summary	1
Table 2.	Suggested connections for unused and not connected pins	6
Table 3.	Absolute maximum ratings	7
Table 4.	Thermal data (per island)	8
Table 5.	Power output.	9
Table 6.	Protections	9
Table 7.	V_{CC} - output diode	10
Table 8.	Switching ($V_{CC} = 13V$; $T_j = 25^{\circ}C$)	10
Table 9.	Logic inputs.	10
Table 10.	Status pin	10
Table 11.	Openload detection.	11
Table 12.	Truth table.	12
Table 13.	Electrical transient requirements	13
Table 14.	Thermal calculation according to the PCB heatsink area	22
Table 15.	Thermal parameters	24
Table 16.	SO-28 mechanical data	25
Table 17.	Document revision history	27

List of figures

Figure 1.	Block diagram	5
Figure 2.	Configuration diagram (top view)	6
Figure 3.	Current and voltage conventions	8
Figure 4.	Status timings	11
Figure 5.	Switching characteristics	11
Figure 6.	Waveforms	14
Figure 7.	Off state output current	15
Figure 8.	High level input current	15
Figure 9.	Input clamp voltage	15
Figure 10.	Turn-on voltage slope	15
Figure 11.	Overvoltage shutdown	15
Figure 12.	Turn-off voltage slope	15
Figure 13.	ILIM vs Tcase	16
Figure 14.	On state resistance vs VCC	16
Figure 15.	Input high level	16
Figure 16.	Input hysteresis voltage	16
Figure 17.	On state resistance vs Tcase	16
Figure 18.	Input low level	16
Figure 19.	Status leakage current	17
Figure 20.	Status low output voltage	17
Figure 21.	Status clamp voltage	17
Figure 22.	Openload On state detection threshold	17
Figure 23.	Openload Off state voltage detection threshold	17
Figure 24.	Application schematic	18
Figure 25.	Openload detection in Off state	20
Figure 26.	Maximum turn-off current versus load inductance	21
Figure 27.	SO-28 PC board	22
Figure 28.	Rthj-amb Vs PCB copper area in open box free air condition	23
Figure 29.	Thermal impedance junction ambient single pulse	23
Figure 30.	Thermal fitting model of a quad channel HSD in SO-28	24
Figure 31.	SO-28 package dimensions	25
Figure 32.	SO-28 tube shipment (no suffix)	26
Figure 33.	SO-28 tape and reel shipment (suffix "TR")	26

1 Block diagram and pin description

Figure 1. Block diagram

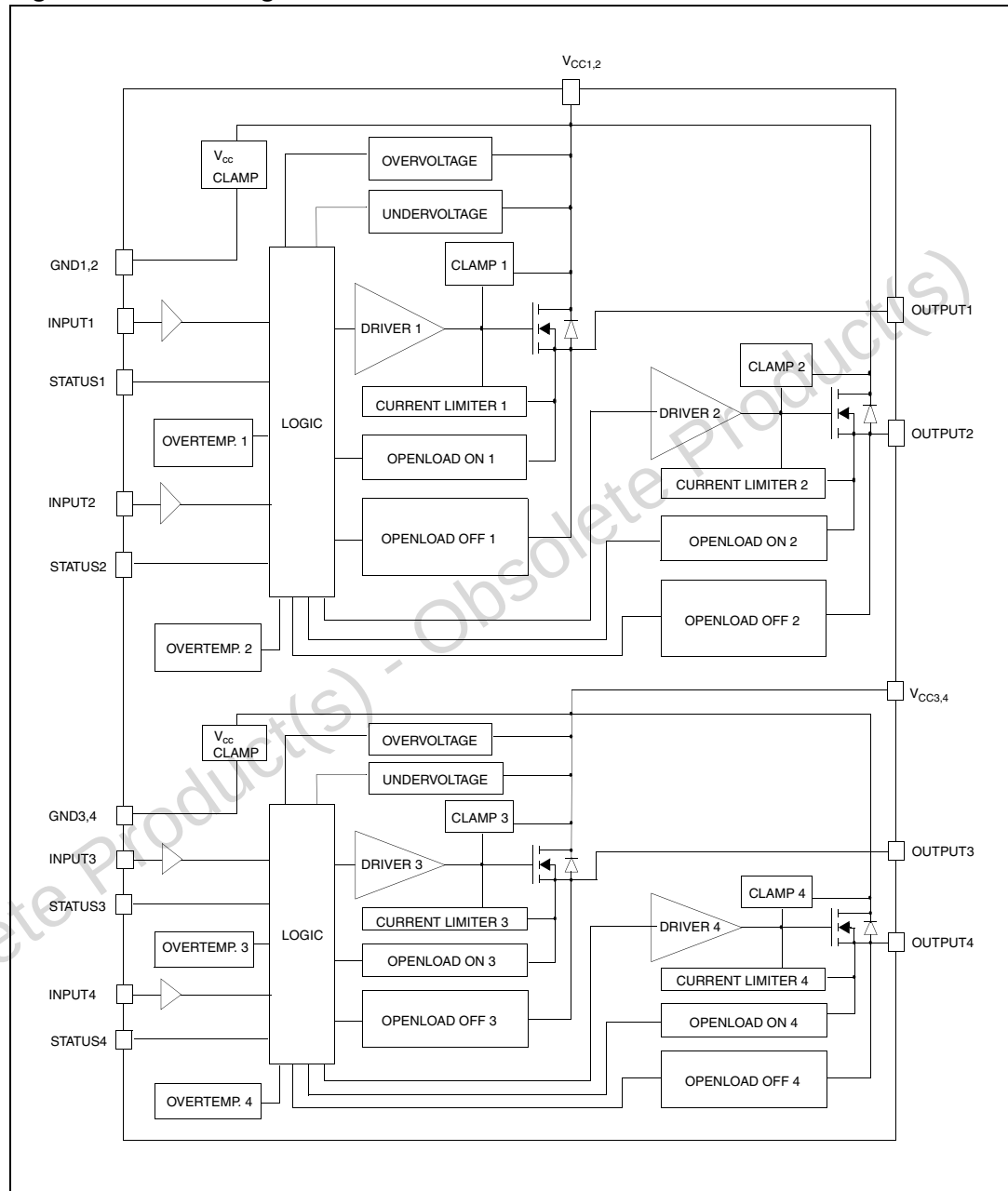


Figure 2. Configuration diagram (top view)

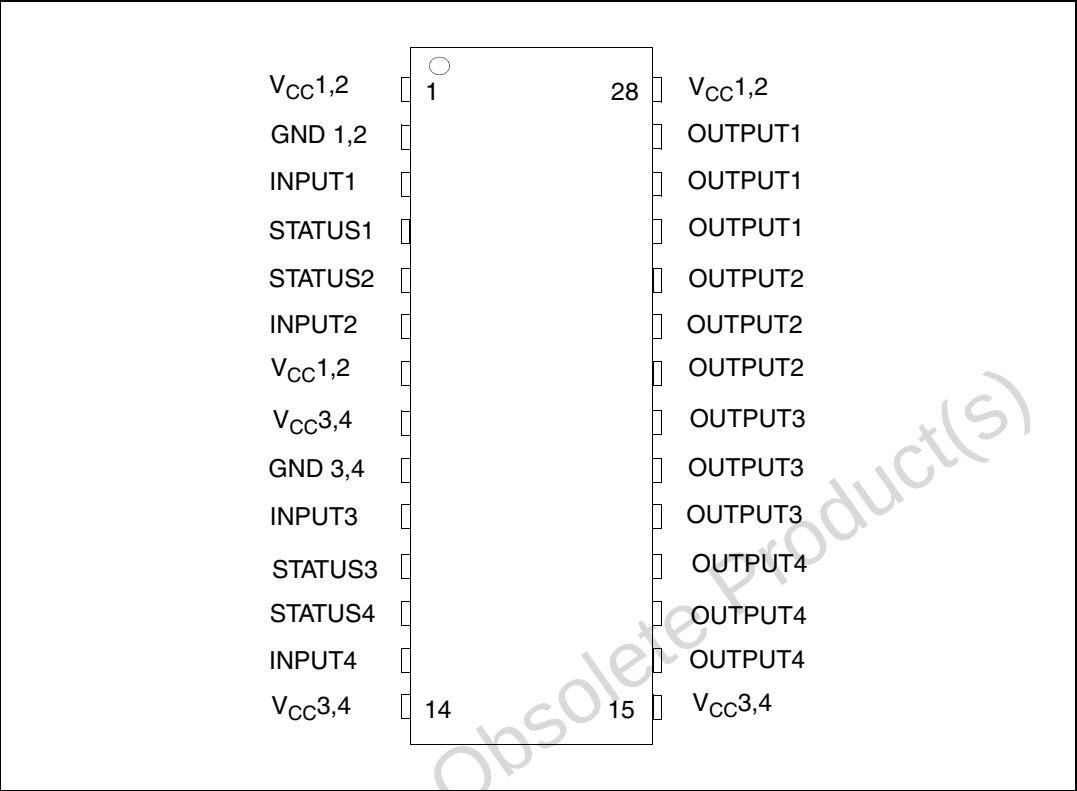


Table 2. Suggested connections for unused and not connected pins

Connection / pin	Status	N.C.	Output	Input
Floating	X	X	X	X
To ground		X		Through 10KΩ resistor

2 Electrical specifications

2.1 Absolute maximum ratings

Stressing the device above the rating listed in the “Absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality document.

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	DC supply voltage	41	V
$-V_{CC}$	Reverse DC supply voltage	- 0.3	V
$-I_{GND}$	DC reverse ground pin current	- 200	mA
I_{OUT}	DC output current	Internally limited	A
$-I_{OUT}$	Reverse DC output current	- 6	A
I_{IN}	DC input current	+/- 10	mA
I_{STAT}	DC Status current	+/- 10	mA
V_{ESD}	Electrostatic discharge (human body model: $R=1.5K\Omega$; $C = 100pF$)		
	- INPUT	4000	V
	- STATUS	4000	V
	- OUTPUT	5000	V
	- V_{CC}	5000	V
E_{MAX}	Maximum switching energy ($L = 2.5mH$; $R_L = 0\Omega$; $V_{bat} = 13.5V$; $T_{jstart} = 150^\circ C$; $I_L = 9A$)	174	mJ
P_{tot}	Power dissipation (per island) at $T_{lead} = 25^\circ C$	6.25	W
T_j	Junction operating temperature	Internally limited	$^\circ C$
T_{stg}	Storage temperature	- 55 to 150	$^\circ C$

2.2 Thermal data

Table 4. Thermal data (per island)

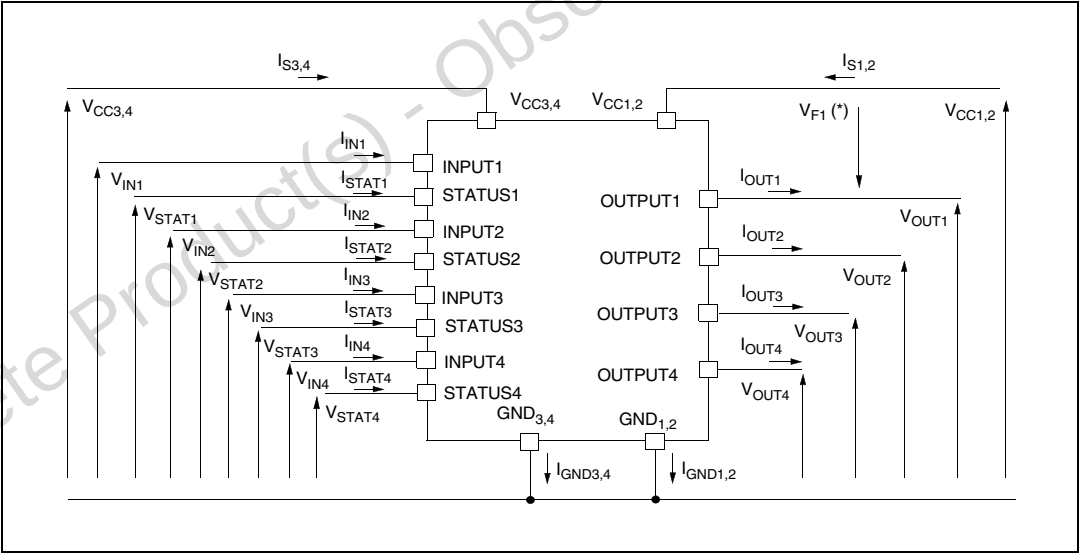
Symbol	Parameter	Value		Unit
$R_{thj-lead}$	Thermal resistance junction-lead	20		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (one chip ON)	60 ⁽¹⁾	44 ⁽²⁾	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient (two chips ON)	46 ⁽¹⁾	31 ⁽²⁾	°C/W

1. When mounted on a standard single-sided FR-4 board with 0.5cm² of Cu (at least 35 μm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.
2. When mounted on a standard single-sided FR-4 board with 6cm² of Cu (at least 35 μm thick) connected to all V_{CC} pins. Horizontal mounting and no artificial air flow.

2.3 Electrical characteristics

Values specified in this section are for 8V < V_{CC} < 36V; -40°C < T_j < 150°C, unless otherwise stated.

Figure 3. Current and voltage conventions



Note: $V_{Fn} = V_{CCn} - V_{OUTn}$ during reverse battery condition.

Table 5. Power output

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC}	Operating supply voltage		5.5	13	36	V
V_{USD}	Undervoltage shutdown		3	4	5.5	V
V_{OV}	Overvoltage shutdown		36			V
R_{ON}	On state resistance	$I_{OUT} = 0.5A$; $T_j = 25^\circ C$ $I_{OUT} = 0.5A$; $V_{CC} > 8V$			150 300	$m\Omega$ $m\Omega$
I_S	Supply current	Off State; $V_{CC} = 13V$; $V_{IN} = V_{OUT} = 0V$		12	40	μA
		Off State; $V_{CC} = 13V$; $V_{IN} = V_{OUT} = 0V$; $T_j = 25^\circ C$		12	25	μA
		On State; $V_{CC} = 13V$; $V_{IN} = 5V$; $I_{OUT} = 0A$		5	7	mA
$I_{L(off1)}$	Off state output current	$V_{IN} = V_{OUT} = 0V$	0		50	μA
$I_{L(off2)}$	Off state output current	$V_{IN} = 0V$; $V_{OUT} = 3.5V$	-75		0	μA
$I_{L(off3)}$	Off state output current	$V_{IN} = V_{OUT} = 0V$; $V_{CC} = 13V$; $T_j = 125^\circ C$			5	μA
$I_{L(off4)}$	Off state output current	$V_{IN} = V_{OUT} = 0V$; $V_{CC} = 13V$; $T_j = 25^\circ C$			3	μA

Table 6. Protections

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
T_{TSD}	Shutdown temperature		150	175	200	$^\circ C$
T_R	Reset temperature		135			$^\circ C$
T_{hyst}	Thermal hysteresis		7	15		$^\circ C$
t_{SDL}	Status delay in overload conditions	$T_j > T_{TSD}$			20	μs
I_{lim}	Current limitation	$V_{CC} = 13V$ $5.5V < V_{CC} < 36V$	0.7	0.9	1.4 1.4	A A
V_{demag}	Turn-off output clamp voltage	$I_{OUT} = 0.5A$	$V_{CC} - 41$	$V_{CC} - 48$	$V_{CC} - 55$	V

Note:

To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device is subjected to abnormal conditions, this software must limit the duration and number of activation cycles.

Table 7. V_{CC} - output diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on voltage	$-I_{OUT} = 0.53A$; $T_J = 150^\circ C$			0.6	V

Table 8. Switching ($V_{CC} = 13V$; $T_J = 25^\circ C$)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$R_L = 26\Omega$ from V_{IN} rising edge to $V_{OUT} = 1.3V$ (see Figure 5)		30		μs
$t_{d(off)}$	Turn-off delay time	$R_L = 26\Omega$ from V_{IN} falling edge to $V_{OUT} = 11.7V$ (see Figure 5)		30		μs
$dV_{OUT}/dt_{(on)}$	Turn-on voltage slope	$R_L = 26\Omega$ from $V_{OUT} = 1.3V$ to $V_{OUT} = 10.4V$ (see Figure 5)		See Figure 10		$V/\mu s$
$dV_{OUT}/dt_{(off)}$	Turn-off voltage slope	$R_L = 26\Omega$ from $V_{OUT} = 11.7V$ to $V_{OUT} = 1.3V$ (see Figure 5)		See Figure 12		$V/\mu s$

Table 9. Logic inputs

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{IL}	Input low level				1.25	V
I_{IL}	Low level input current	$V_{IN} = 1.25V$	1			μA
V_{IH}	Input high level		3.25			V
I_{IH}	High level input current	$V_{IN} = 3.25V$			10	μA
$V_{I(hyst)}$	Input hysteresis voltage		0.5			V
V_{ICL}	Input clamp voltage	$I_{IN} = 1mA$ $I_{IN} = -1mA$	6	6.8 - 0.7	8	V V

Table 10. Status pin

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{STAT}	Status low output voltage	$I_{STAT} = 1.6mA$			0.5	V
I_{LSTAT}	Status leakage current	Normal operation; $V_{STAT} = 5V$			10	μA
C_{STAT}	Status pin Input capacitance	Normal operation; $V_{STAT} = 5V$			100	pF
V_{SCL}	Status clamp voltage	$I_{STAT} = 1mA$ $I_{STAT} = -1mA$	6	6.8 - 0.7	8	V V

Table 11. Openload detection

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{OL}	Openload On state detection threshold	$V_{IN} = 5V$	20	40	80	mA
$t_{DOL(on)}$	Openload On state detection delay	$I_{OUT} = 0A$			200	μs
V_{OL}	Openload Off state voltage detection threshold	$V_{IN} = 0V$	1.5	2.5	3.5	V
$t_{DOL(off)}$	Openload detection delay at turn-off				1000	μs

Figure 4. Status timings

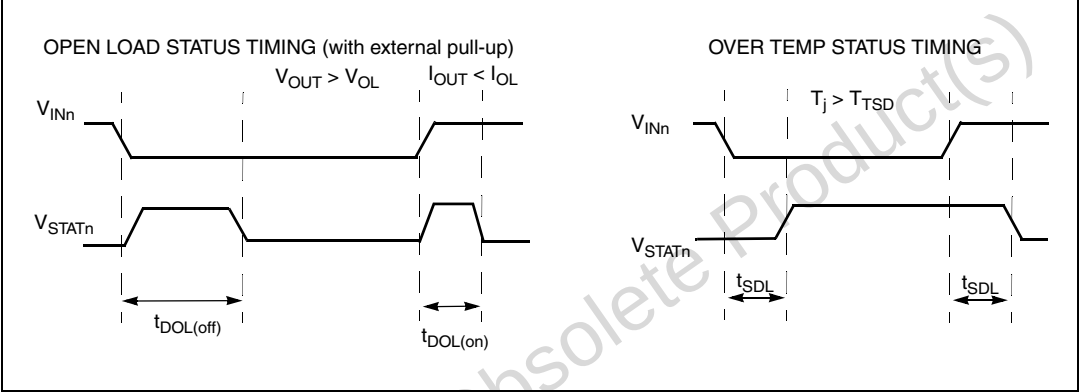


Figure 5. Switching characteristics

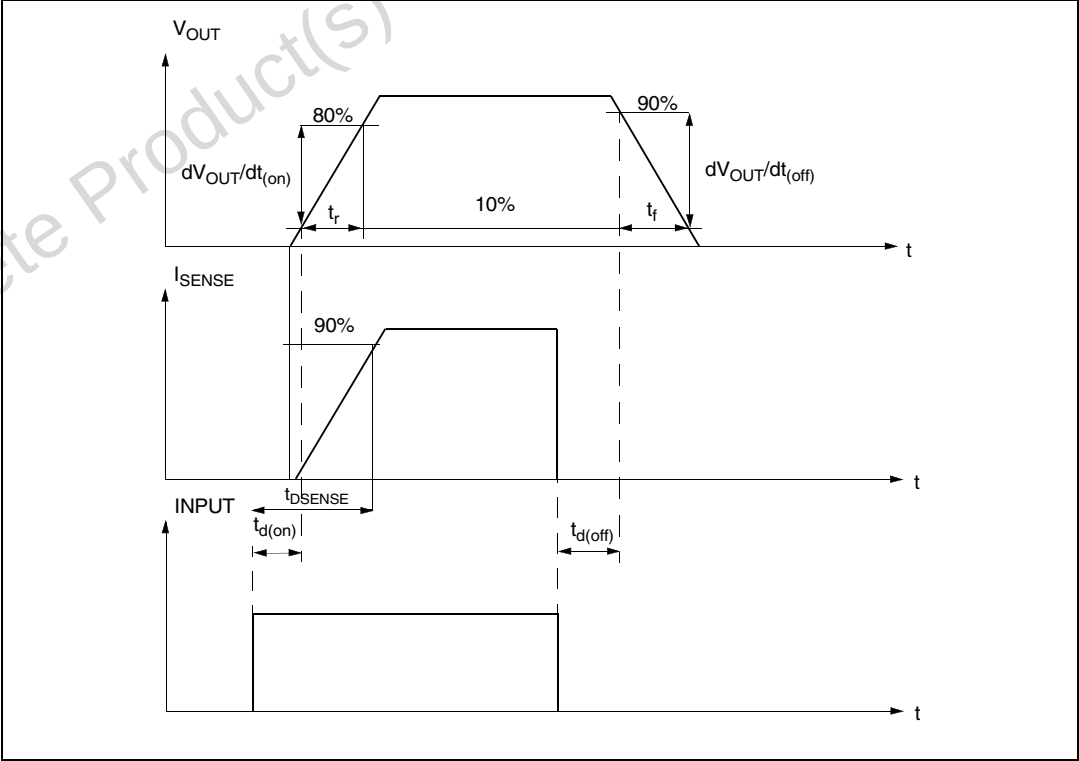


Table 12. Truth table

Conditions	Input	Output	Status
Normal operation	L	L	H
	H	H	H
Current limitation	L	L	H
	H	X	$(T_j < T_{TSD})$ H
	H	X	$(T_j > T_{TSD})$ L
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output voltage > V_{OL}	L	H	L
	H	H	H
Output current < I_{OL}	L	L	H
	H	H	L

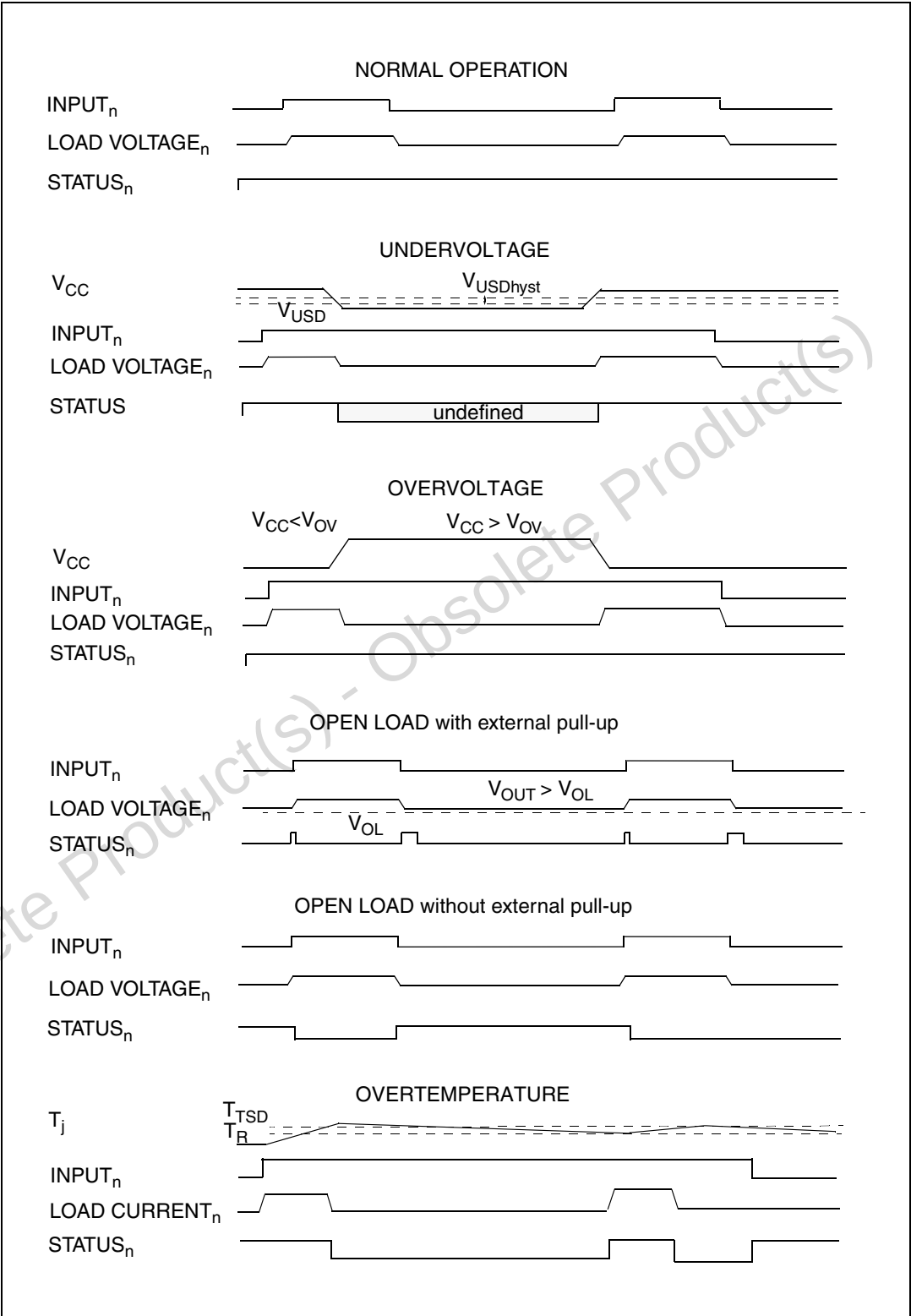
Table 13. Electrical transient requirements

ISO T/R 7637/1 Test pulse	Test level				Delays and impedance
	I	II	III	IV	
1	- 25V	- 50V	- 75V	- 100V	2ms, 10Ω
2	+ 25V	+ 50V	+ 75V	+ 100V	0.2ms, 10Ω
3a	- 25V	- 50V	- 100V	- 150V	0.1μs, 50Ω
3b	+ 25V	+ 50V	+ 75V	+ 100V	0.1μs, 50Ω
4	- 4V	- 5V	- 6V	- 7V	100ms, 0.01Ω
5	+ 26.5V	+ 46.5V	+ 66.5V	+ 86.5V	400ms, 2Ω

ISO T/R 7637/1 Test pulse	Test level			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

Class	Contents
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

Figure 6. Waveforms



2.4 Electrical characteristics curves

Figure 7. Off state output current

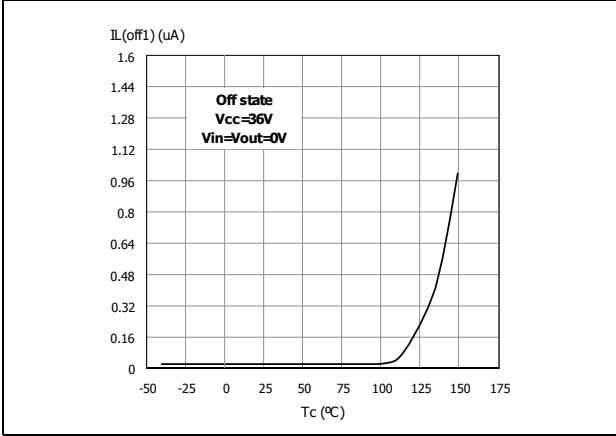


Figure 8. High level input current

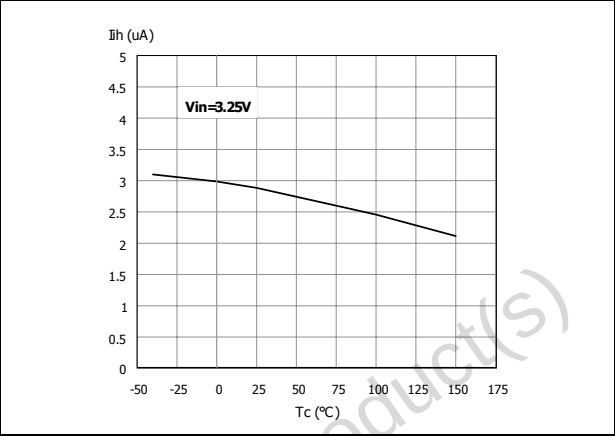


Figure 9. Input clamp voltage

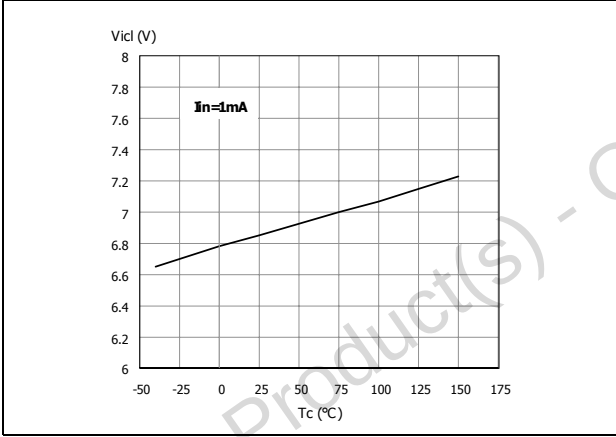


Figure 10. Turn-on voltage slope

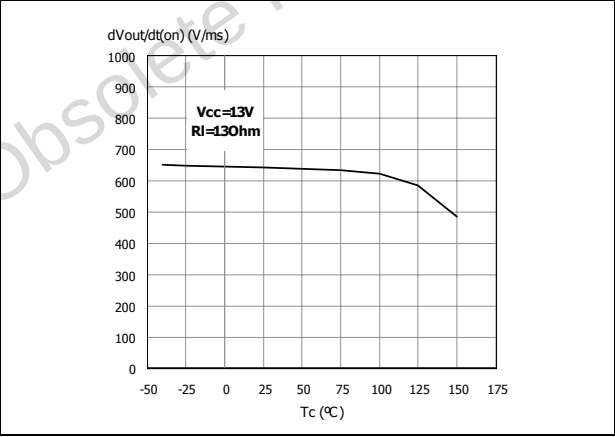


Figure 11. Overvoltage shutdown

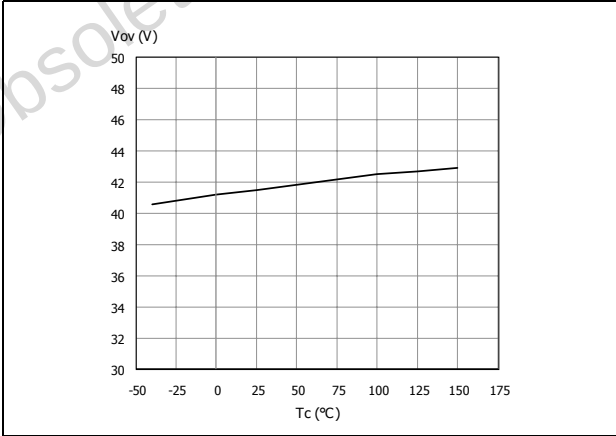


Figure 12. Turn-off voltage slope

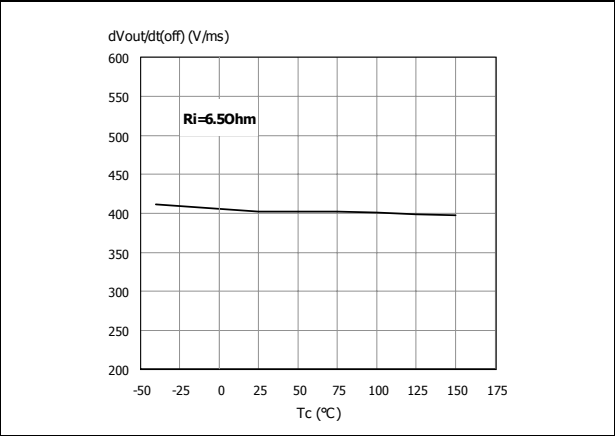


Figure 13. I_{LIM} vs T_{case}

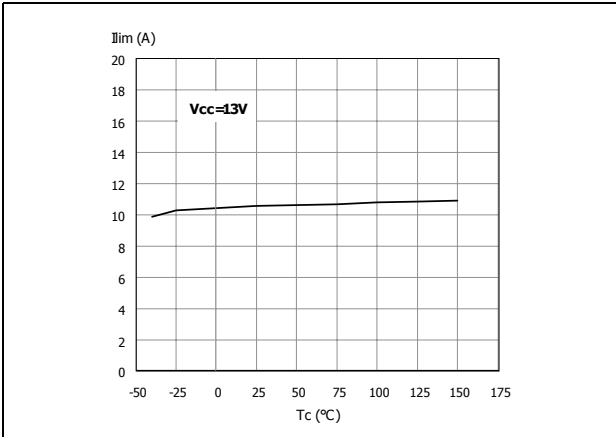


Figure 14. On state resistance vs V_{CC}

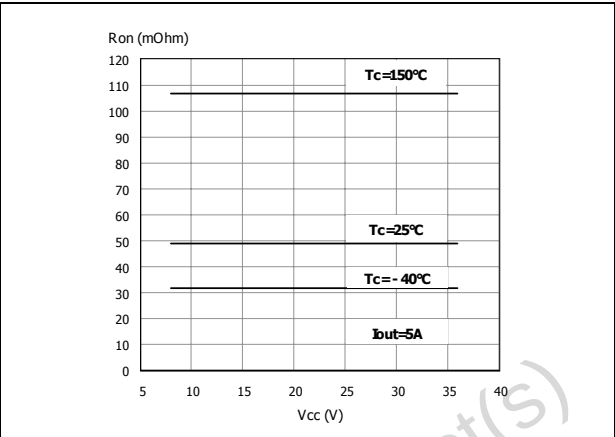


Figure 15. Input high level

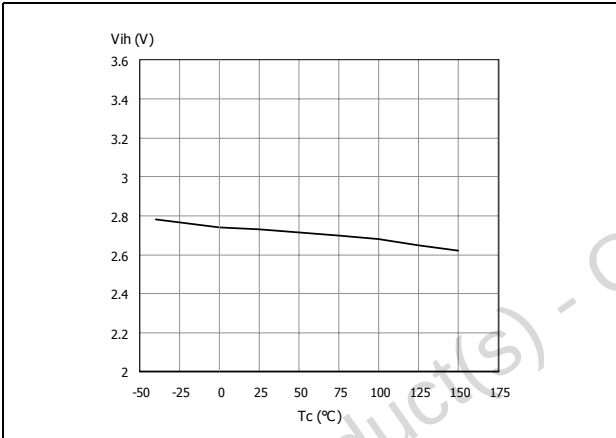


Figure 16. Input hysteresis voltage

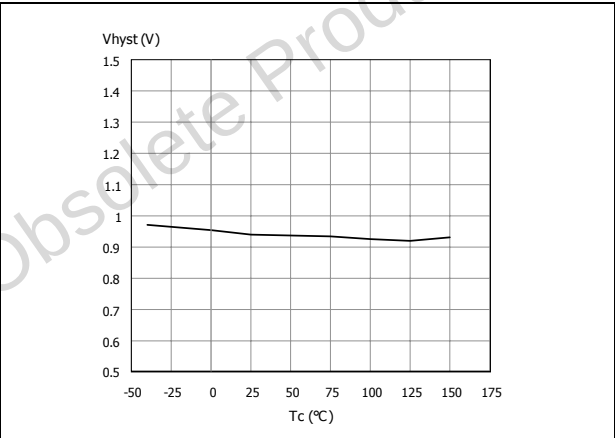


Figure 17. On state resistance vs T_{case}

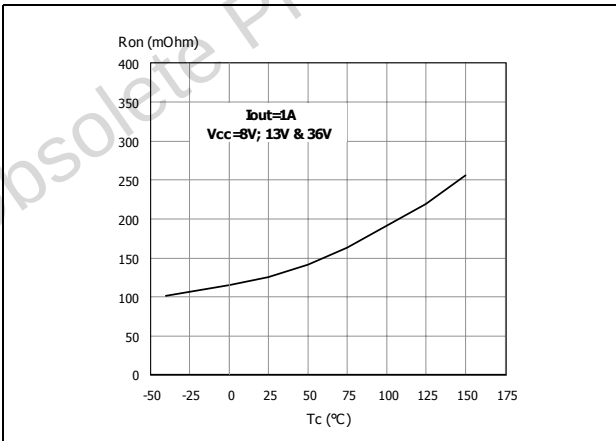


Figure 18. Input low level

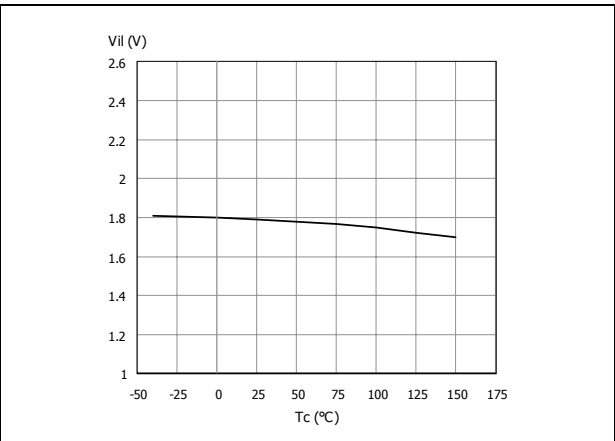


Figure 19. Status leakage current

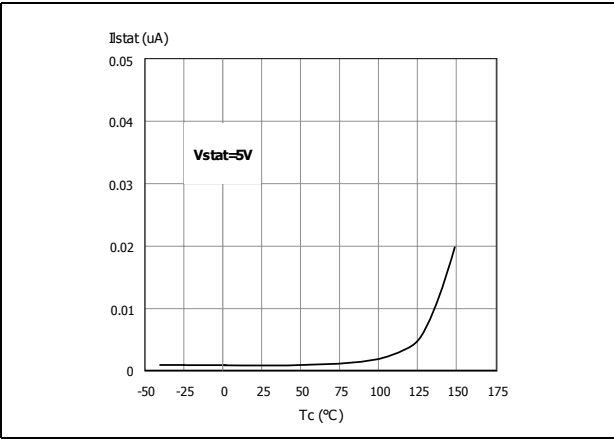


Figure 20. Status low output voltage

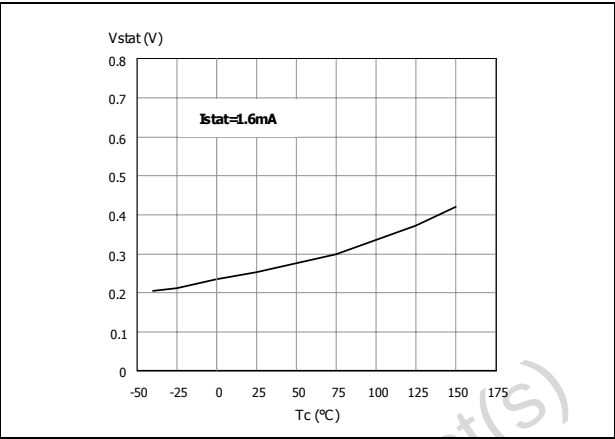


Figure 21. Status clamp voltage

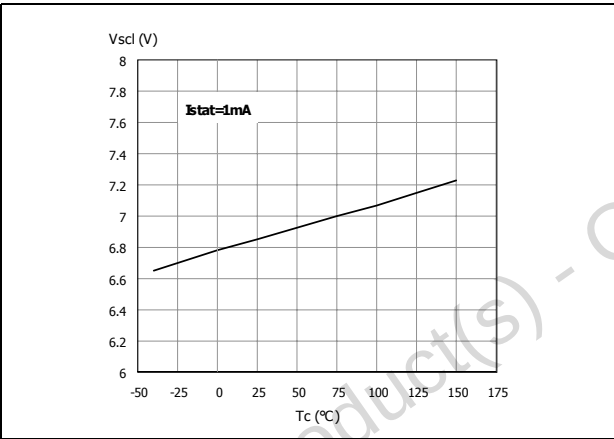


Figure 22. Openload On state detection threshold

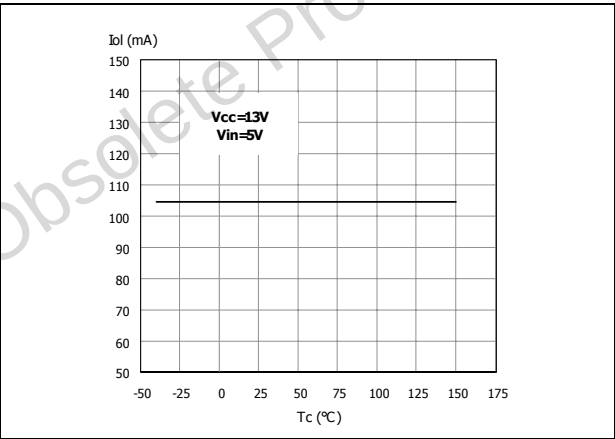
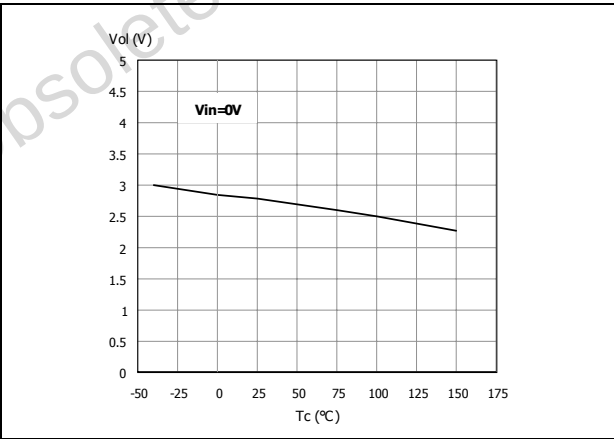
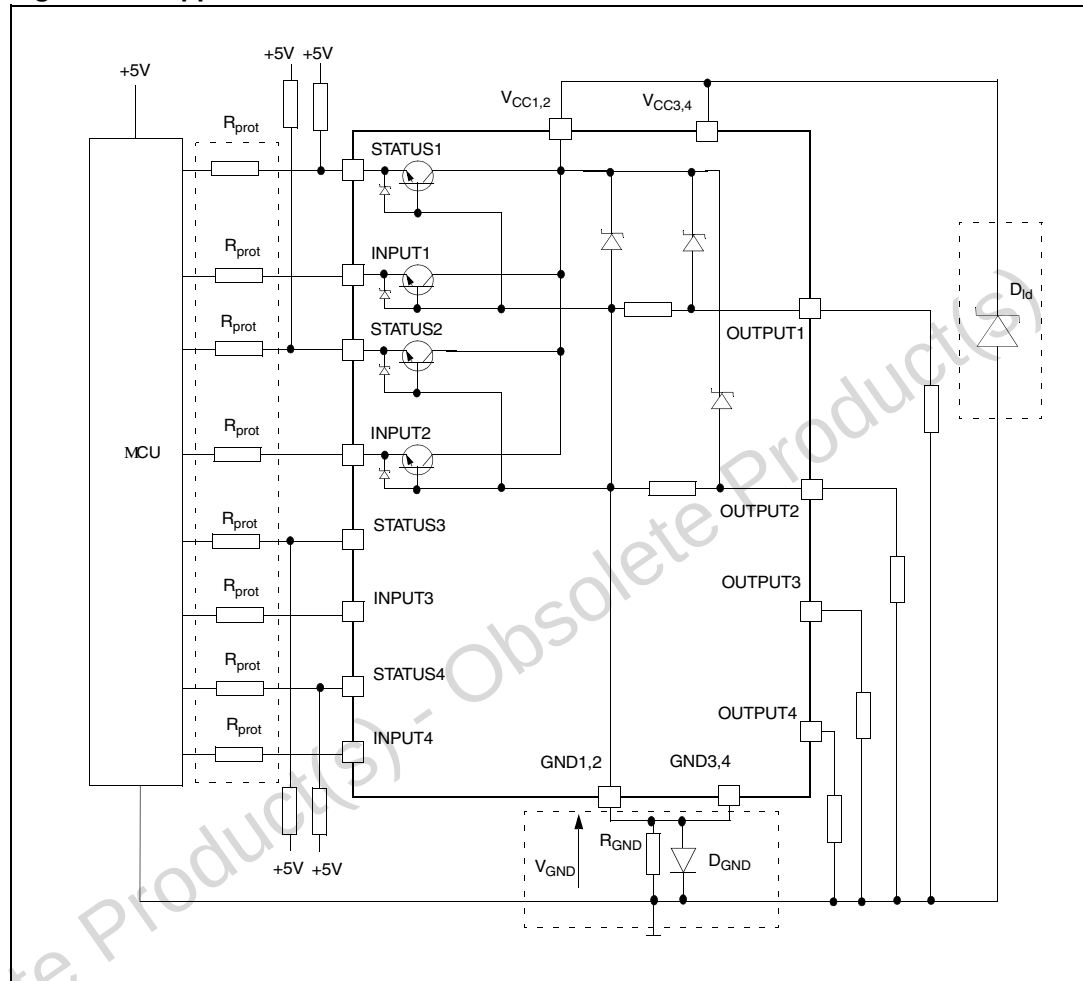


Figure 23. Openload Off state voltage detection threshold



3 Application information

Figure 24. Application schematic



Note: Channels 3 & 4 have the same internal circuit as channel 1 & 2.

3.1 GND protection network against reverse battery

This section provides two solutions for implementing a ground protection network against reverse battery.

3.1.1 Solution 1: a resistor in the ground line (R_{GND} only)

This can be used with any type of load.

The following show how to dimension the R_{GND} resistor:

1. $R_{GND} \leq 600\text{mV} / 2 (I_{S(on)max})$
2. $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R_{GND} (when $V_{CC} < 0$ during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that, if the microprocessor ground is not shared by the device ground, then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation requires the use of a large resistor, or several devices have to share the same resistor, then ST suggests using solution 2 below.

3.1.2 Solution 2: a diode (D_{GND}) in the ground line

A resistor ($R_{GND} = 1k\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load. This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift (j600mV) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network. Series resistor in INPUT and STATUS lines are also required to prevent that, during battery voltage transient, the current exceeds the Absolute Maximum Rating. Safest configuration for unused INPUT and STATUS pin is to leave them unconnected.

3.2 Load dump protection

D_{ld} is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the V_{CC} maximum DC rating. The same applies if the device is subject to transients on the V_{CC} line that are greater than those shown in the ISO T/R 7637/1 table.

3.3 MCU I/O protection

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the μC I/O pins from latching up.

The value of these resistors is a compromise between the leakage current of μC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of μC I/Os:

$$-V_{CCpeak} / I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Example

For the following conditions:

$$V_{CCpeak} = -100V$$

$$I_{latchup} \geq 20mA$$

$$V_{OH\mu C} \geq 4.5V$$

$$5k\Omega \leq R_{prot} \leq 65k\Omega$$

Recommended values are:

$$R_{prot} = 10k\Omega$$

3.4 Open load detection in off state

Off state open load detection requires an external pull-up resistor (R_{PU}) connected between OUTPUT pin and a positive supply voltage (V_{PU}) like the +5V line used to supply the microprocessor.

The external resistor has to be selected according to the following requirements:

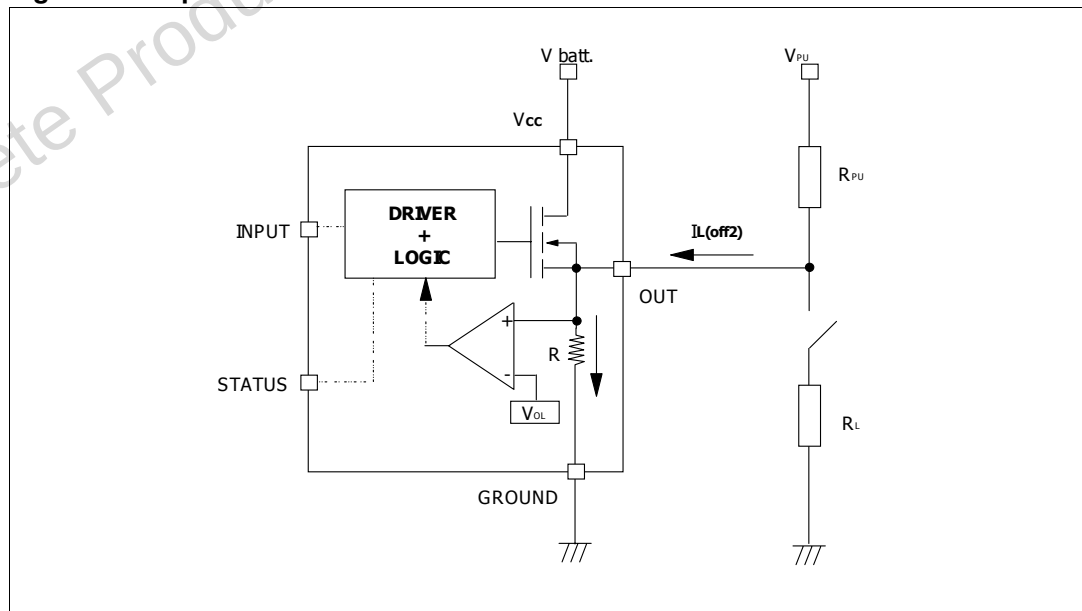
1) no false open load indication when load is connected: in this case we have to avoid V_{OUT} to be higher than V_{OLmin} ; this results in the following condition

$$V_{OUT} = (V_{PU} / (R_L + R_{PU}))R_L < V_{OLmin}.$$

2) no misdetection when load is disconnected: in this case the V_{OUT} has to be higher than V_{OLmax} ; this results in the following condition $R_{PU} < (V_{PU} - V_{OLmax}) / I_{L(off2)}$.

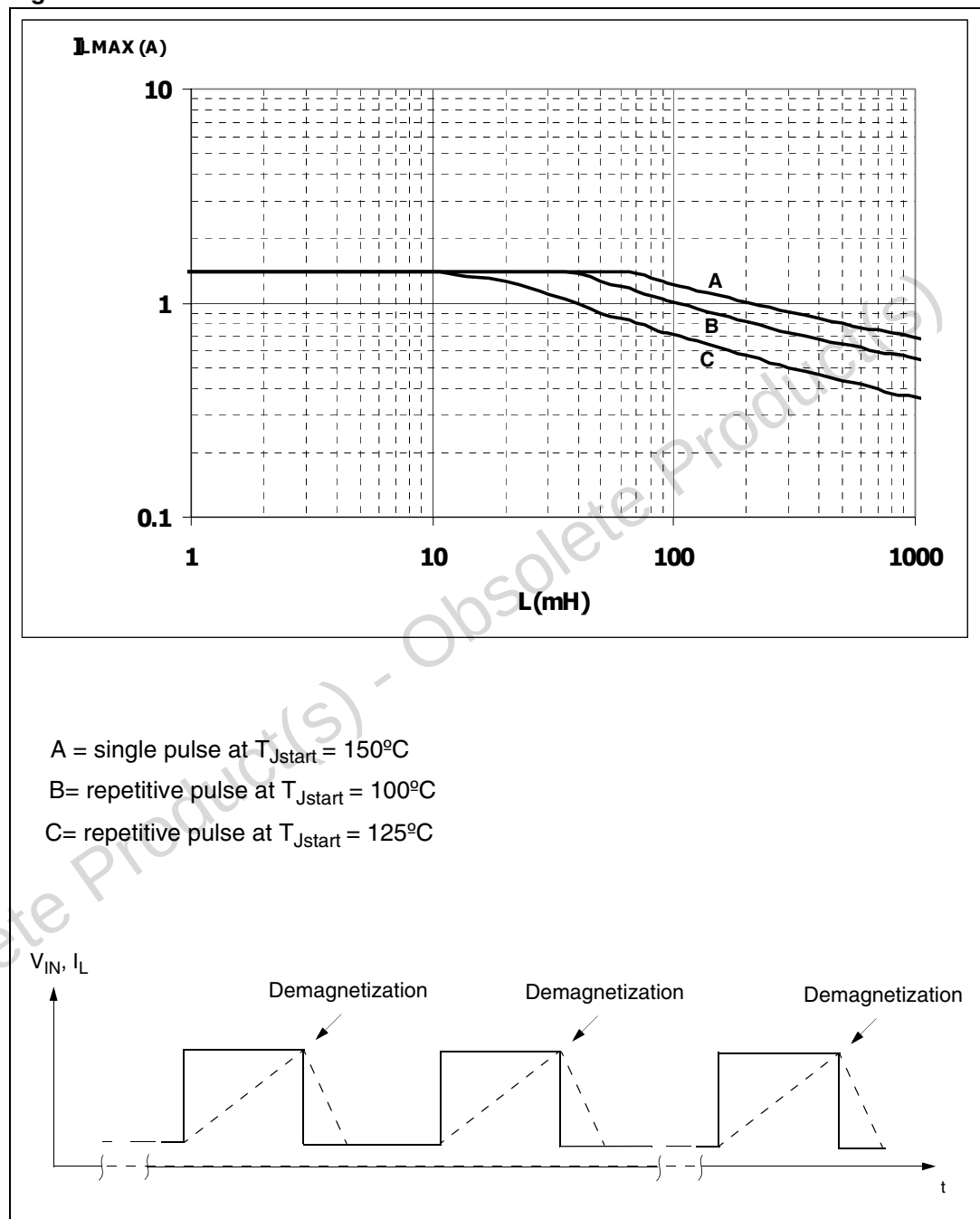
Because $I_{S(OFF)}$ may significantly increase if V_{out} is pulled high (up to several mA), the pull-up resistor R_{PU} should be connected to a supply that is switched OFF when the module is in standby.

Figure 25. Openload detection in Off state



3.5 Maximum demagnetization energy ($V_{CC} = 13.5V$)

Figure 26. Maximum turn-off current versus load inductance



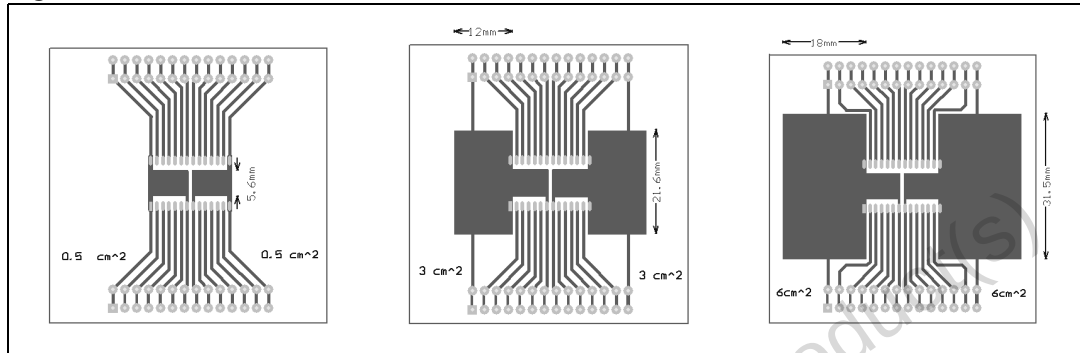
Note: Values are generated with $R_L = 0\Omega$

In case of repetitive pulses, T_{Jstart} (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves B and C.

4 Package and PCB thermal data

4.1 SO-28 thermal data

Figure 27. SO-28 PC board



Note: Layout condition of R_{th} and Z_{th} measurements (PCB FR4 area = 58mm x 58mm, PCB thickness = 2mm, Cu thickness = 35 μ m, Copper areas: 0.5 cm², 3 cm², 6 cm²).

Table 14. Thermal calculation according to the PCB heatsink area

Chip 1	Chip 2	T_{jchip1}	T_{jchip2}	Note
ON	OFF	$R_{thA} \times P_{dchip1} + T_{amb}$	$R_{thC} \times P_{dchip1} + T_{amb}$	
OFF	ON	$R_{thC} \times P_{dchip2} + T_{amb}$	$R_{thA} \times P_{dchip2} + T_{amb}$	
ON	ON	$R_{thB} \times (P_{dchip1} + P_{dchip2}) + T_{amb}$	$R_{thB} \times (P_{dchip1} + P_{dchip2}) + T_{amb}$	$P_{dchip1} = P_{dchip2}$
ON	ON	$(R_{thA} \times P_{dchip1}) + R_{thC} \times P_{dchip2} + T_{amb}$	$(R_{thA} \times P_{dchip2}) + R_{thC} \times P_{dchip1} + T_{amb}$	$P_{dchip1} \neq P_{dchip2}$

R_{thA} = thermal resistance junction to ambient with one chip ON

R_{thB} = thermal resistance junction to ambient with both chips ON and $P_{dchip1} = P_{dchip2}$

R_{thC} = mutual thermal resistance

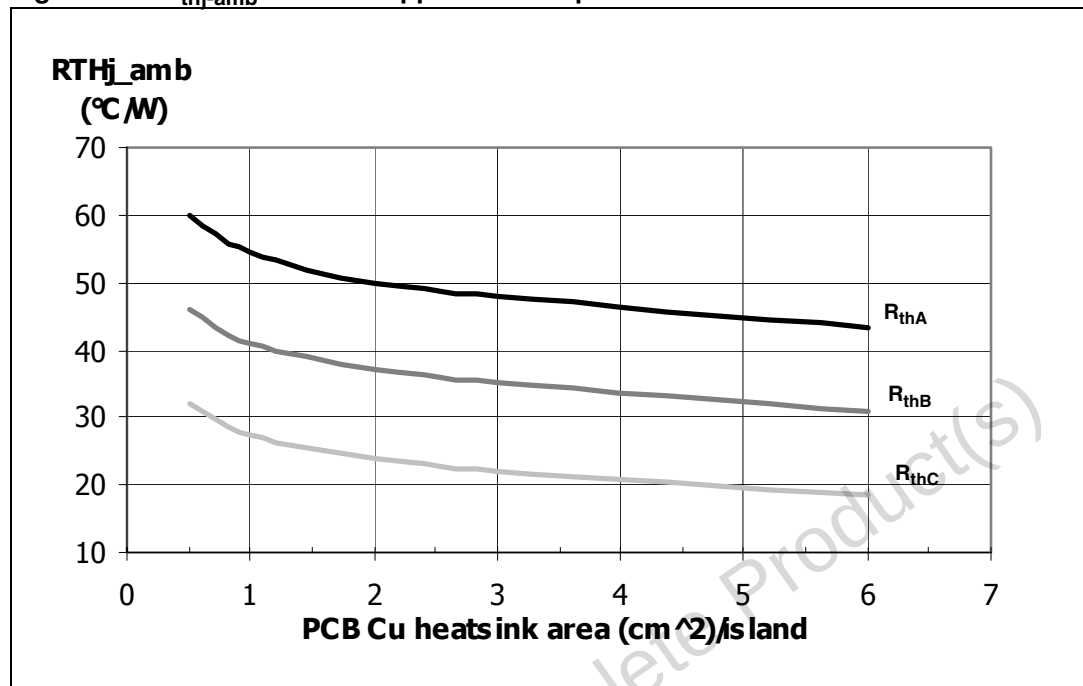
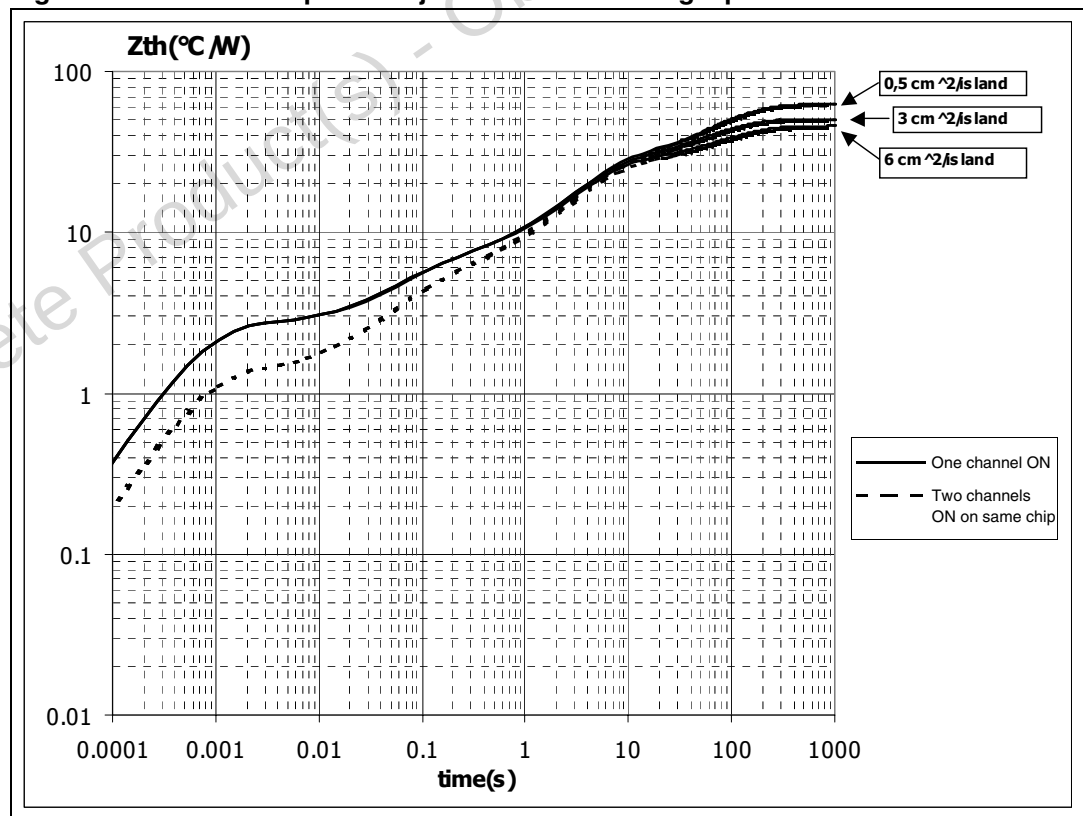
Figure 28. $R_{thj-amb}$ Vs PCB copper area in open box free air condition

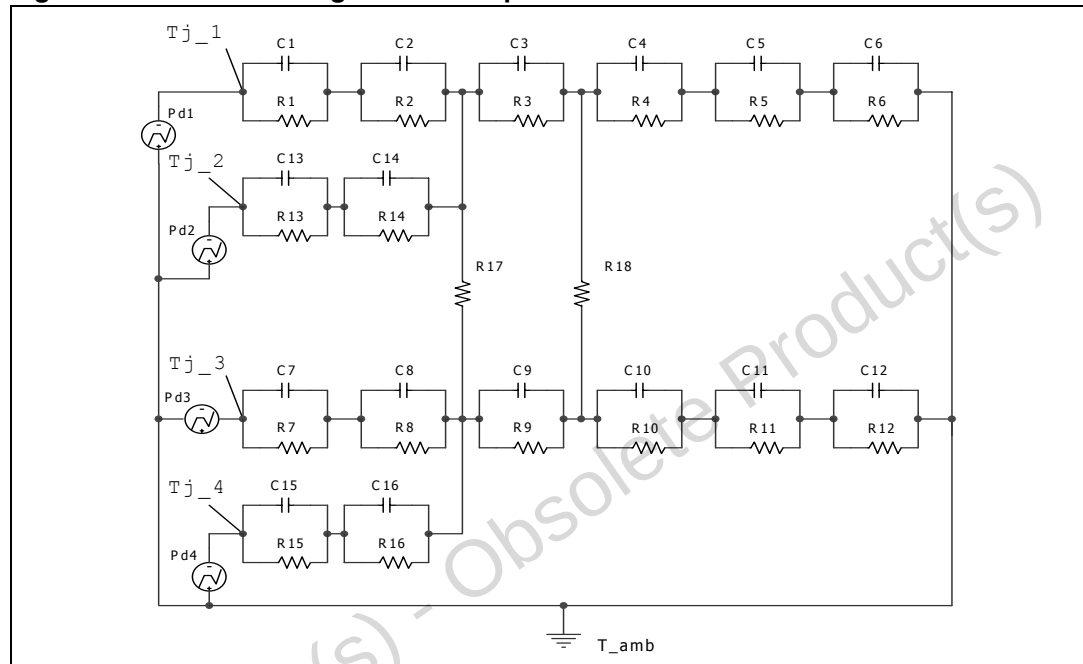
Figure 29. Thermal impedance junction ambient single pulse



Equation 1: pulse calculation formula

$$Z_{TH\delta} = R_{TH} \cdot \delta + Z_{THtp}(1 - \delta)$$

$$\text{where } \delta = t_p / T$$

Figure 30. Thermal fitting model of a quad channel HSD in SO-28**Table 15. Thermal parameters**

Area / island (cm ²)	Footprint	6
R1 = R7 = R13 = R15 (°C/W)	0.35	
R2 = R8 = R14 = R16 (°C/W)	1.8	
R3 = R9 (°C/W)	4.5	
R4 = R10 (°C/W)	11	
R5 = R11 (°C/W)	15	
R6 = R12 (°C/W)	30	13
C1 = C7 = C13 = C15 (W.s/°C)	0.0001	
C2 = C8 = C14 = C16 (W.s/°C)	7E-04	
C3 = C9 (W.s/°C)	6E-03	
C4 = C10 (W.s/°C)	0.2	
C5 = C11 (W.s/°C)	1.5	
C6 = C12 (W.s/°C)	5	8
R17 = R18 (°C/W)	150	

5 Package and packing information

5.1 ECOPACK® packages

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second-level interconnect. The category of Second-Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Figure 31. SO-28 package dimensions

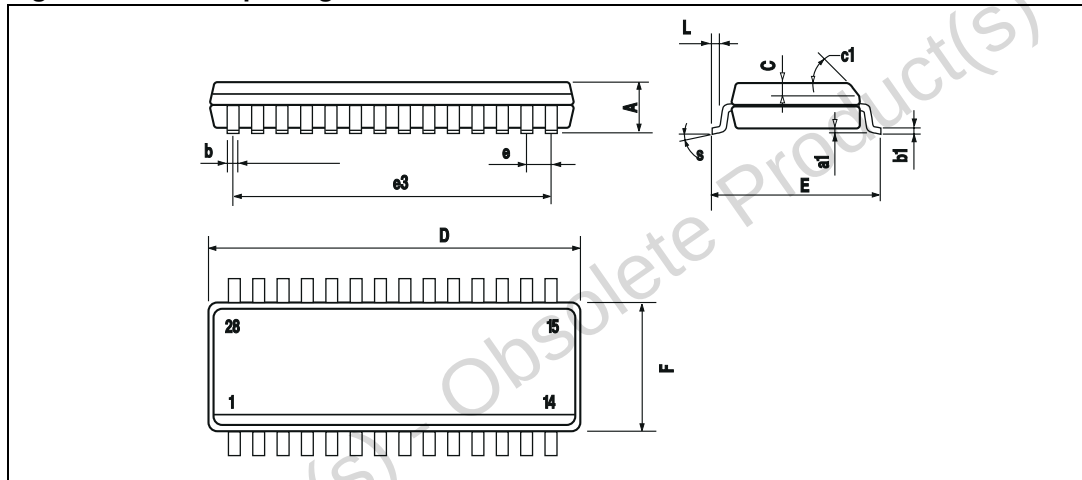


Table 16. SO-28 mechanical data

Symbol	Millimeters		
	Min.	Typ.	Max.
A			2.65
a1	0.10		0.30
b	0.35		0.49
b1	0.23		0.32
C		0.50	
c1		45° (typ.)	
D	17.7		18.1
E	10.00		10.65
e		1.27	
e3		16.51	
F	7.40		7.60
L	0.40		1.27
S		8° (max.)	

5.2 SO-28 packing information

Figure 32. SO-28 tube shipment (no suffix)

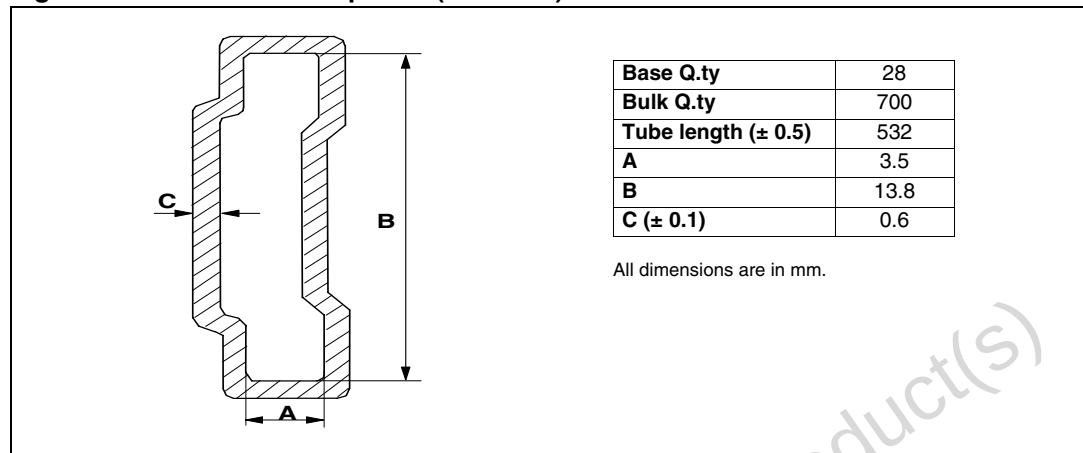
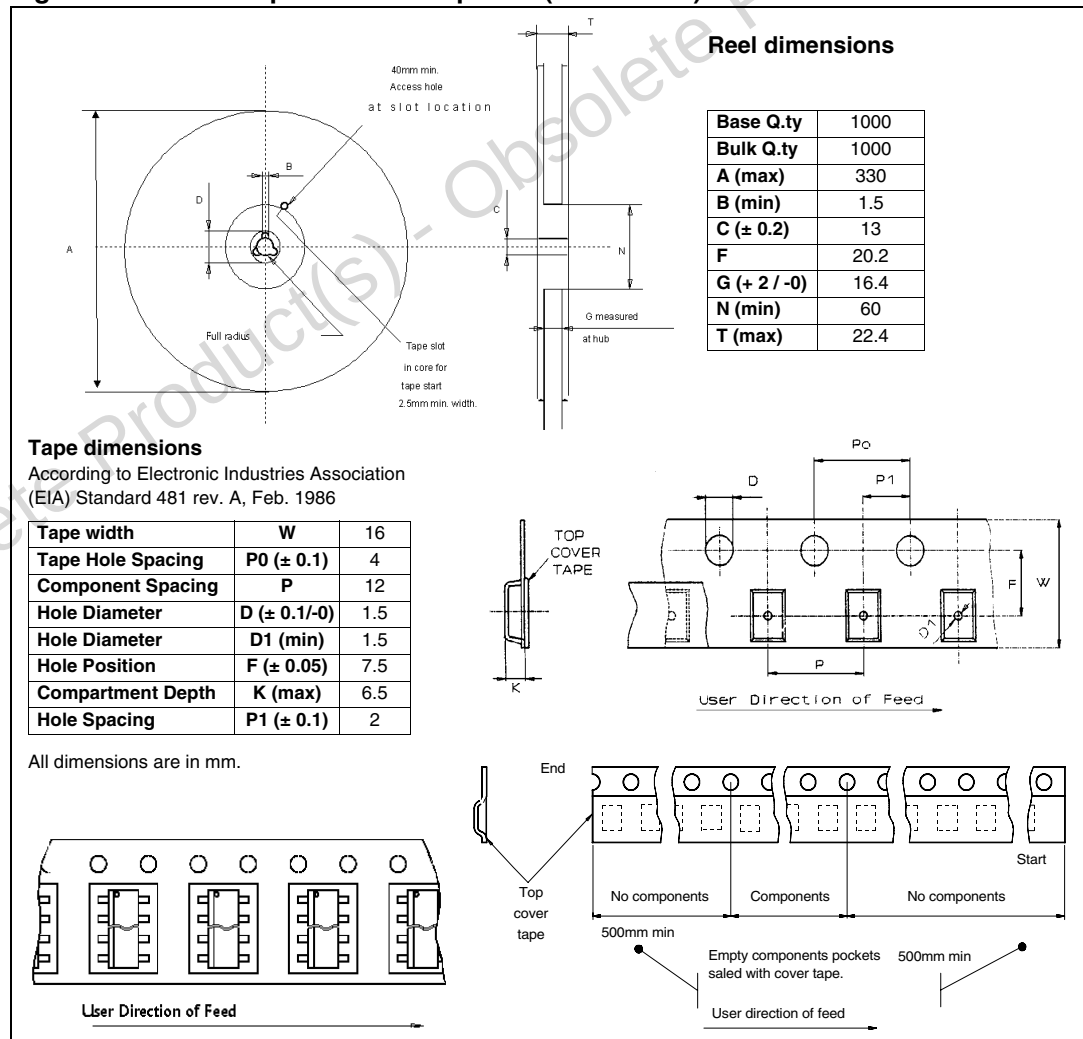


Figure 33. SO-28 tape and reel shipment (suffix "TR")



6 Revision history

Table 17. Document revision history

Date	Revision	Changes
09-Sep-2004	1	Initial release.
03-May-2006	2	Minor changes. Current and voltage convention update (page 3). Configuration diagram (top view) & suggested connections for unused and n.c. pins insertion (page 3). 6 cm ² Cu condition insertion in thermal data table (page 4). V _{CC} - output diode section update (page 4). Protections note insertion (page 5) Revision history table insertion (page 20). Disclaimers update (page 21).
02-Dec-2008	3	Document reformatted and restructured. Added contents, list of tables and figures. Added <i>ECOPACK® packages</i> information.
24-Sep-2013	4	Updated Disclaimer.

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